

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = +25^\circ C$
-30V	1.5 $\Omega$ @ $V_{GS} = -4.5V$	-0.3 A
	2.5 $\Omega$ @ $V_{GS} = -2.5V$	-0.2 A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Load Switch
- Portable Applications
- Power Management Functions

## Features

- 0.4mm Ultra Low Profile Package for Thin Application
- 0.48mm<sup>2</sup> Package Footprint, 16 Times Smaller Than SOT23
- Low  $V_{GS(th)}$ , can be Driven Directly from a Battery
- Low  $R_{DS(ON)}$
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e4)**
- Weight: 0.00043 grams (Approximate)

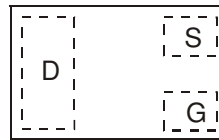
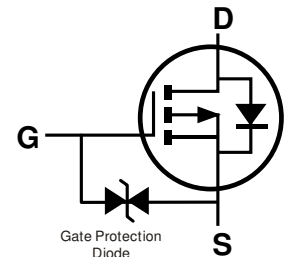


ESD PROTECTED

X2-DFN0806-3



Bottom View


 Top View  
Package Pin Configuration


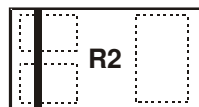
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP32D5LFA-7B	X2-DFN0806-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information


 Top View  
Bar Denotes Gate  
and Source Side

R2= Product Type Marking Code

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-0.3	A
		T <sub>A</sub> = +70°C		-0.2	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-1.5	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P <sub>D</sub>	360	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	353	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-100	nA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	—	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>	—	0.9	1.5	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -200mA
			1.2	2.5		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -100mA
			2.5	7.5		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -50mA
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	—	—	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -10mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	—	40.9	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	4.7	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	3.6	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	0.7	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -200mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.2	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	20	—	ns	V <sub>DS</sub> = -15V, I <sub>D</sub> = -200mA V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	40	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	144	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	58	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

NEW PRODUCT

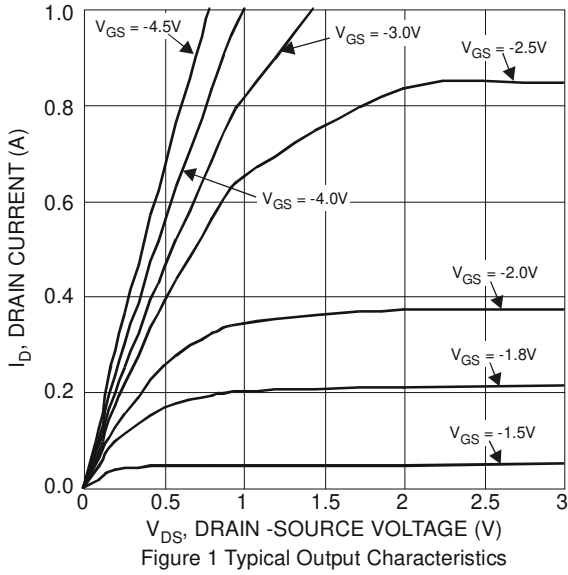


Figure 1 Typical Output Characteristics

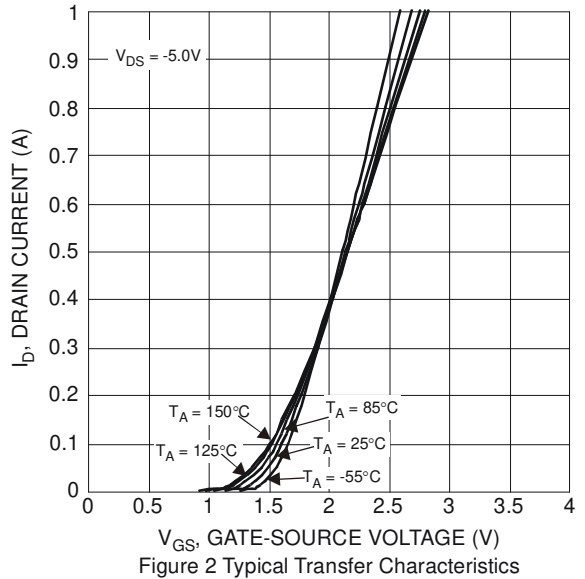


Figure 2 Typical Transfer Characteristics

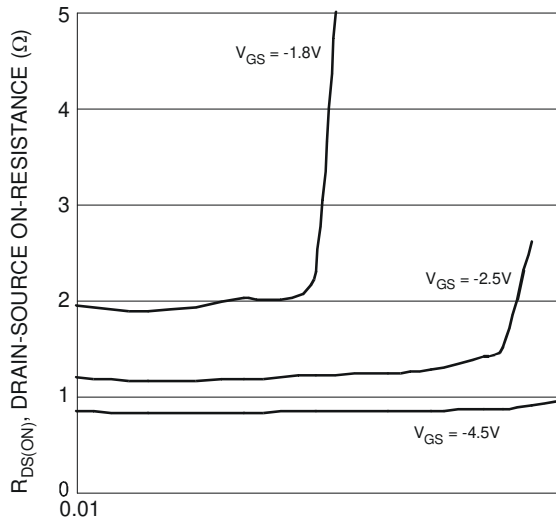


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

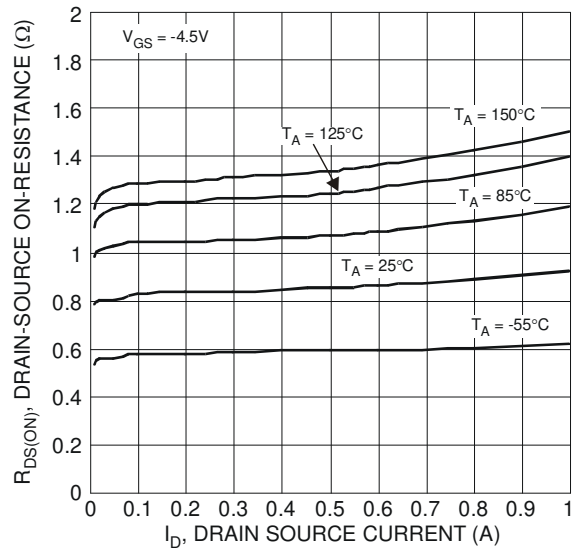


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

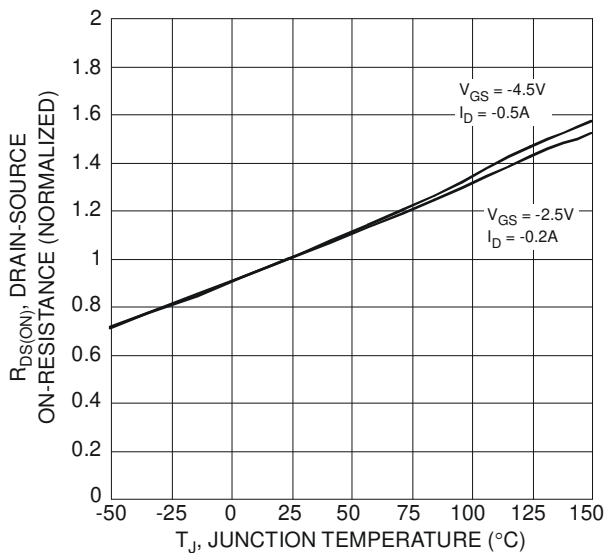


Figure 5 On-Resistance Variation with Temperature

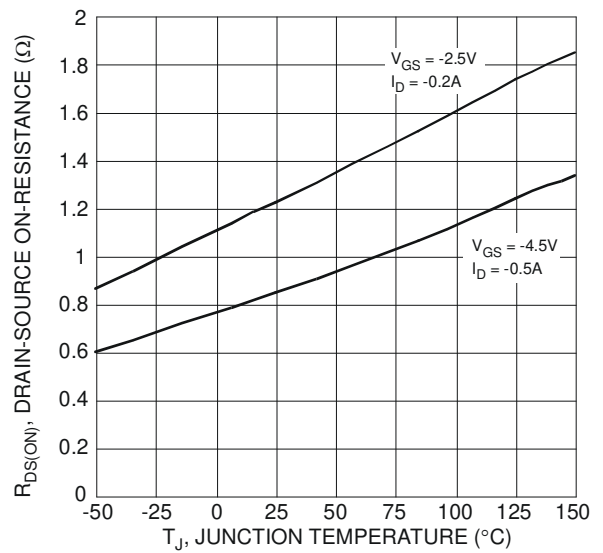


Figure 6 On-Resistance Variation with Temperature

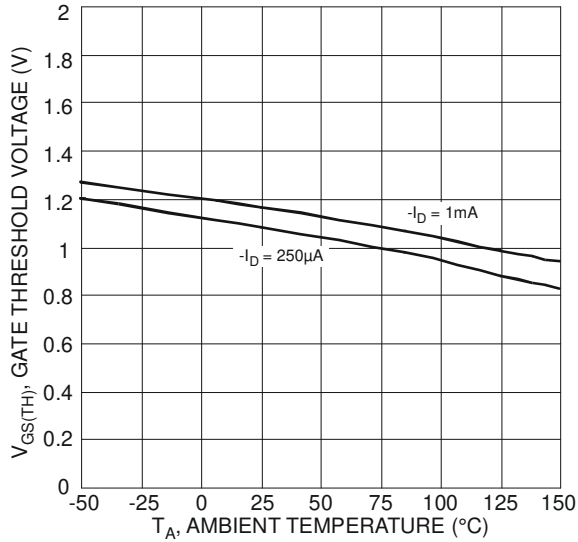


Figure 7 Gate Threshold Variation vs. Ambient Temperature

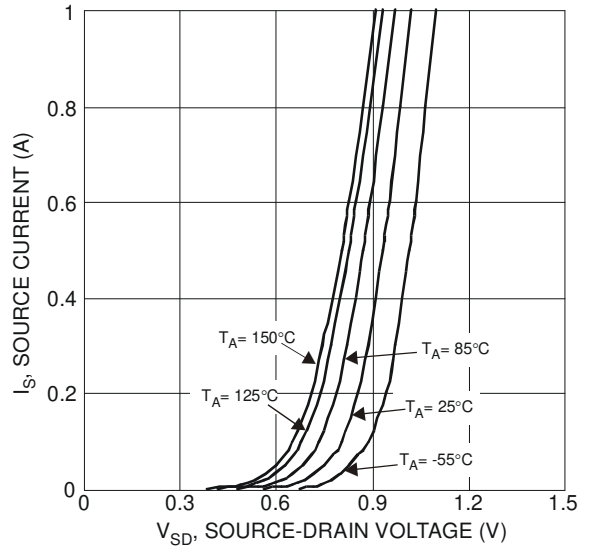


Figure 8 Diode Forward Voltage vs. Current

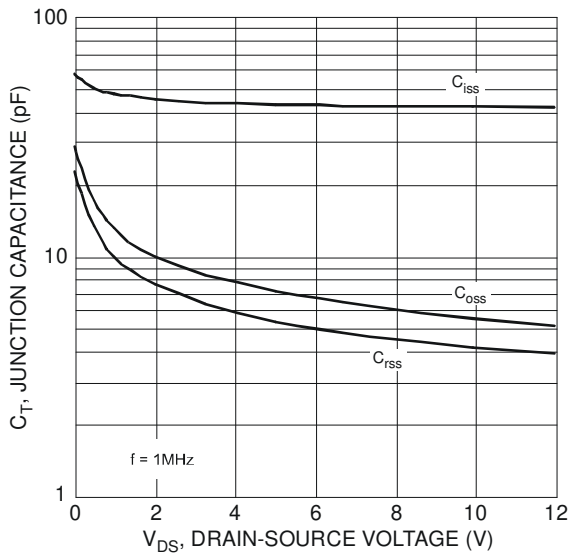


Figure 9 Typical Junction Capacitance

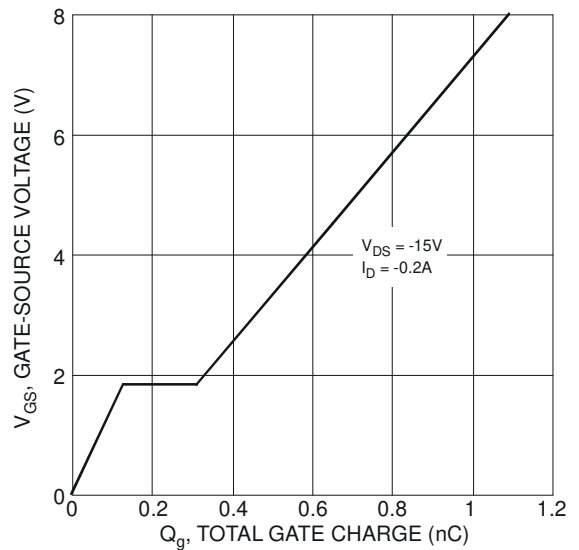


Figure 10 Gate-Charge Characteristics

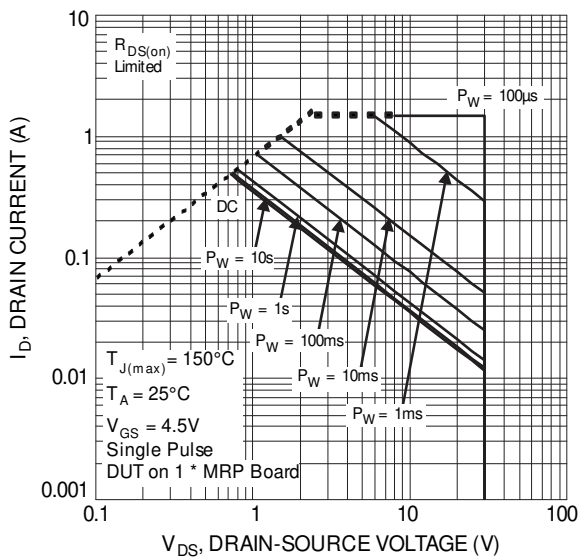
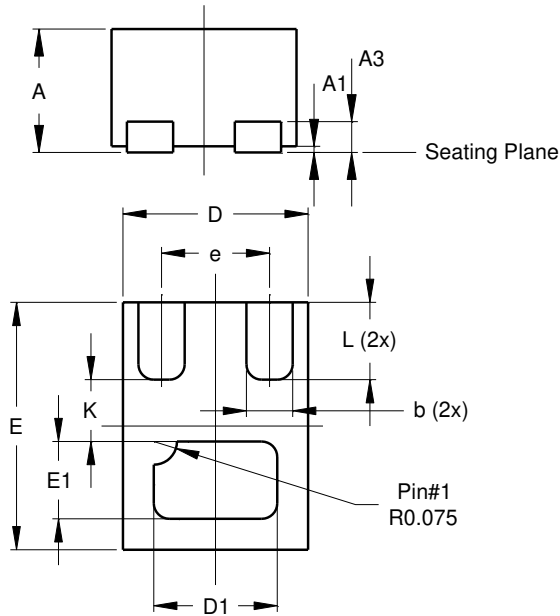


Figure 11 SOA, Safe Operation Area

NEW PRODUCT

**Package Outline Dimensions**

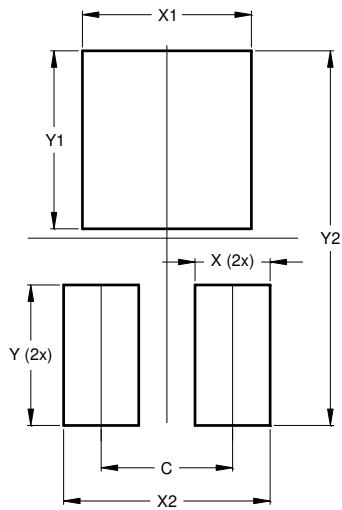
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
X1	0.450
X2	0.550
Y	0.375
Y1	0.475
Y2	1.000

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